

The RF MOSFET Line

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

MRF6522-10R1

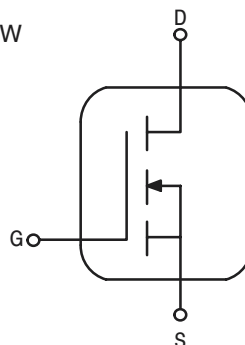
**960 MHz, 10 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFET**



**CASE 458C-03, STYLE 1
NI-200Z**

Designed for Class A-AB common source, linear power amplifiers in the 960 MHz range. The MRF6522-10R1 has been specifically designed for use in Communications Network (GSM) base stations. The package offers the advantage of SMD.

- Specified 26 Volts, 960 MHz, Class AB Characteristics
Output Power = 10 Watts CW
Power Gain = 15 dB Min @ 960 MHz, 10 Watts CW
Drain Efficiency = 48% Min @ 960 MHz, 10 Watts CW
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- S-Parameter Characterization at High Bias Levels
- Bottom Side Source Eliminates DC Isolators, Reducing Common Mode Inductances
- In Tape and Reel. R1 Suffix = 500 Units per 12 mm, 7 inch Reel.



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	65	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	29 0.17	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (1)	$R_{\theta JC}$	4.0	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0$ Vdc, $I_D = 0.2$ mA)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 26$ Vdc, $V_{GS} = 0$ Vdc)	I_{DSS}	—	—	1.0	μAdc
Gate-Source Leakage Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$ Vdc)	I_{GSS}	—	—	1.0	μAdc

(1) Thermal resistance is determined under specified RF operating condition.

NOTE – CAUTION – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



ELECTRICAL CHARACTERISTICS continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = 10\text{ V}$, $I_D = 50\text{ }\mu\text{A}$)	$V_{GS(th)}$	1.25	3.0	4.0	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 100\text{ mA}$)	$V_{GS(Q)}$	2.25	4.0	5.0	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$)	$V_{DS(on)}$	—	—	0.9	Vdc

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{iss}	—	17	—	pF
Output Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{oss}	—	10	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.9	—	pF

FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)

Common–Source Power Gain ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	G_{ps}	15	17	—	dB
Drain Efficiency ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	η	48	50	—	%
Input Return Loss ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	IRL	—	—	–9	dB

TYPICAL CHARACTERISTICS

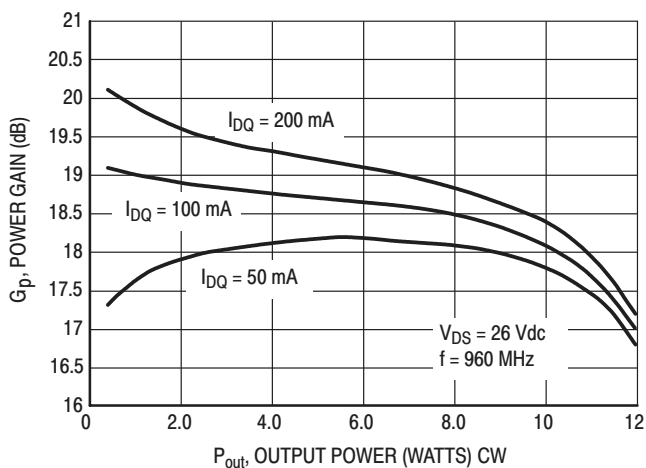


Figure 1. Power Gain versus Output Power

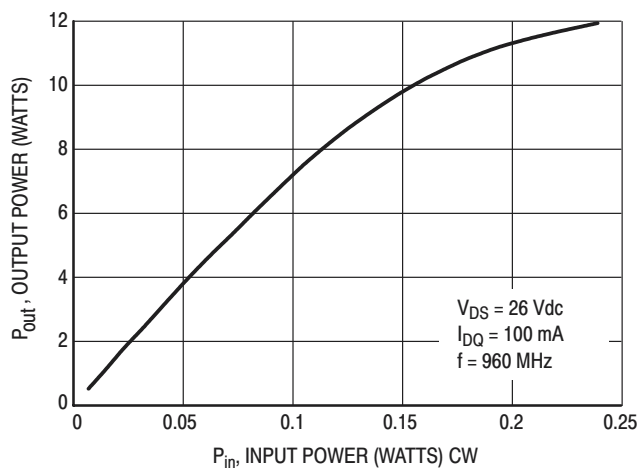


Figure 2. Output Power versus Input Power

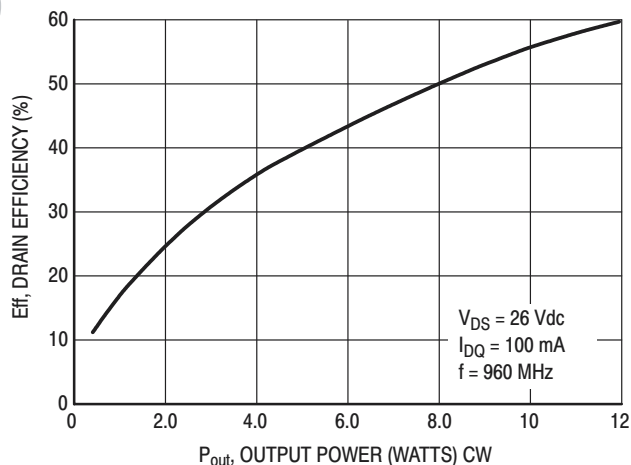


Figure 3. Drain Efficiency versus Output Power

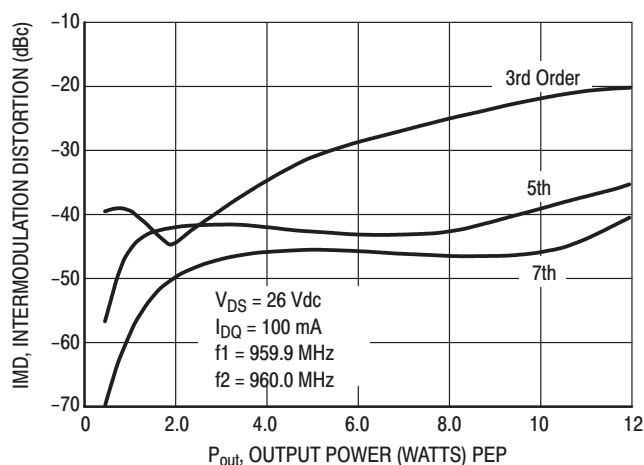
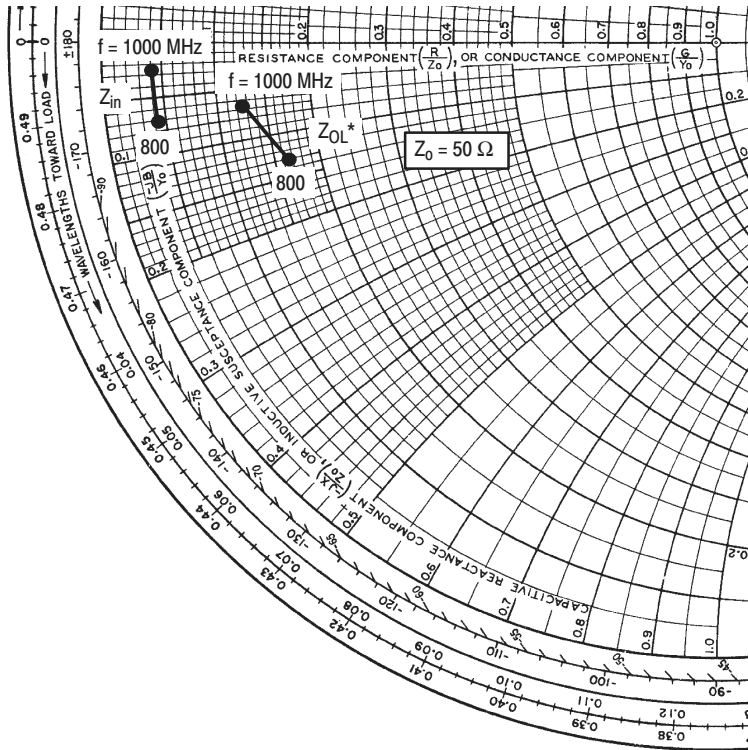


Figure 4. Intermodulation Distortion Products versus Output Power



f MHz	Z _{in} Ohms	Z _{OL} * Ohms
800	2.20 – j3.00	8.50 – j6.20
825	2.20 – j2.80	8.43 – j6.15
850	2.20 – j2.60	8.35 – j6.10
875	2.20 – j2.40	8.28 – j6.08
900	2.20 – j2.20	8.20 – j6.05
925	2.19 – j1.86	7.95 – j5.70
950	2.13 – j1.68	7.50 – j4.75
975	2.03 – j1.45	6.90 – j3.58
1000	2.00 – j1.00	6.50 – j3.00

Z_{in} = Complex conjugate of source impedance.
 Z_{OL}* = Complex conjugate of the optimum load impedance into which the device operates at a given output power, voltage, current and frequency.

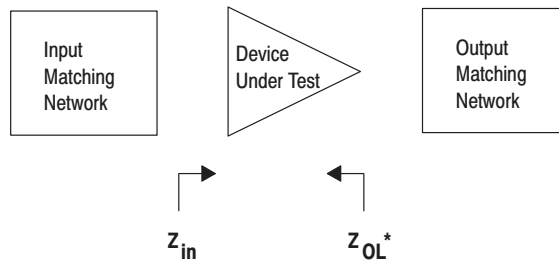


Figure 5. Series Equivalent Input and Output Impedance

Table 1. Common Source S-Parameters at $V_{DS} = 12$ Vdc, $I_D = 100$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.794	-158	2.77	54	0.050	-29	0.720	-150
0.525	0.800	-159	2.61	52	0.049	-32	0.730	-151
0.550	0.807	-160	2.45	49	0.048	-33	0.738	-152
0.575	0.811	-161	2.31	48	0.047	-35	0.746	-153
0.600	0.816	-162	2.18	46	0.046	-37	0.755	-154
0.625	0.822	-163	2.06	44	0.045	-38	0.763	-155
0.650	0.826	-164	1.95	42	0.043	-40	0.770	-156
0.675	0.832	-165	1.85	40	0.042	-41	0.779	-157
0.700	0.836	-166	1.75	39	0.041	-41	0.785	-158
0.725	0.841	-166	1.66	37	0.040	-42	0.793	-159
0.750	0.846	-167	1.58	35	0.039	-44	0.800	-160
0.775	0.851	-168	1.51	34	0.038	-45	0.805	-161
0.800	0.855	-168	1.44	32	0.037	-46	0.812	-162
0.825	0.858	-169	1.37	31	0.036	-47	0.818	-163
0.850	0.863	-170	1.31	29	0.035	-48	0.824	-164
0.875	0.866	-171	1.25	28	0.034	-49	0.830	-165
0.900	0.869	-172	1.20	27	0.033	-50	0.835	-166
0.925	0.872	-172	1.15	25	0.031	-51	0.840	-166
0.950	0.876	-173	1.10	24	0.030	-52	0.846	-167
0.975	0.879	-174	1.06	23	0.029	-52	0.850	-168
1.000	0.882	-174	1.02	22	0.028	-53	0.853	-169

Table 2. Common Source S-Parameters at $V_{DS} = 12$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.784	-164	3.49	59	0.041	-22	0.690	-158
0.525	0.789	-165	3.29	57	0.040	-25	0.697	-159
0.550	0.794	-166	3.11	55	0.040	-26	0.705	-160
0.575	0.798	-167	2.94	53	0.038	-26	0.711	-160
0.600	0.802	-167	2.79	51	0.037	-28	0.719	-161
0.625	0.806	-168	2.65	50	0.037	-30	0.726	-162
0.650	0.811	-169	2.52	48	0.036	-31	0.732	-162
0.675	0.814	-169	2.40	46	0.035	-32	0.740	-163
0.700	0.819	-170	2.28	45	0.034	-32	0.747	-164
0.725	0.823	-171	2.18	43	0.034	-34	0.753	-164
0.750	0.827	-171	2.08	42	0.032	-36	0.760	-165
0.775	0.831	-172	1.99	40	0.032	-36	0.765	-166
0.800	0.834	-172	1.90	39	0.031	-36	0.772	-166
0.825	0.838	-173	1.82	37	0.031	-38	0.778	-167
0.850	0.842	-174	1.74	36	0.029	-38	0.783	-168
0.875	0.845	-174	1.67	35	0.028	-39	0.790	-169
0.900	0.850	-175	1.61	33	0.028	-39	0.797	-169
0.925	0.852	-175	1.54	32	0.027	-41	0.801	-170
0.950	0.854	-176	1.48	31	0.027	-42	0.807	-170
0.975	0.859	-176	1.43	30	0.025	-41	0.810	-171
1.000	0.861	-177	1.38	28	0.025	-42	0.815	-171

Table 3. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 100$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.832	-155	4.05	56	0.033	-25	0.687	-135
0.525	0.836	-156	3.81	54	0.033	-27	0.697	-137
0.550	0.841	-157	3.58	51	0.034	-28	0.707	-138
0.575	0.845	-159	3.38	49	0.032	-31	0.718	-140
0.600	0.849	-160	3.19	47	0.031	-32	0.728	-141
0.625	0.853	-161	3.02	45	0.030	-34	0.737	-143
0.650	0.856	-162	2.86	43	0.029	-35	0.746	-144
0.675	0.861	-163	2.71	42	0.028	-37	0.755	-145
0.700	0.865	-164	2.57	40	0.028	-37	0.762	-147
0.725	0.868	-165	2.44	38	0.026	-38	0.771	-148
0.750	0.871	-166	2.32	37	0.025	-40	0.779	-149
0.775	0.875	-166	2.21	35	0.025	-41	0.786	-150
0.800	0.877	-167	2.11	33	0.023	-41	0.793	-151
0.825	0.880	-168	2.02	32	0.022	-43	0.800	-152
0.850	0.884	-169	1.92	30	0.022	-43	0.808	-154
0.875	0.886	-170	1.84	29	0.021	-44	0.815	-155
0.900	0.889	-171	1.76	27	0.020	-43	0.820	-156
0.925	0.892	-171	1.68	26	0.020	-46	0.826	-157
0.950	0.894	-172	1.61	24	0.019	-45	0.832	-158
0.975	0.897	-173	1.55	23	0.018	-47	0.837	-159
1.000	0.899	-173	1.49	22	0.017	-48	0.842	-160

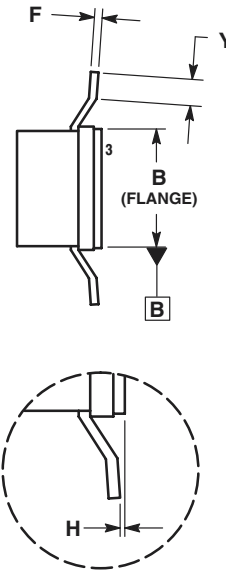
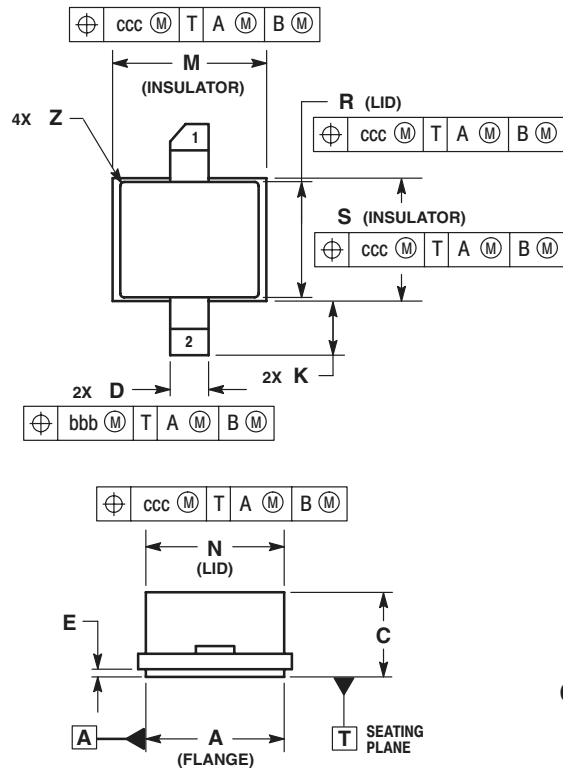
Table 4. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.824	-160	5.02	59	0.029	-21	0.627	-143
0.525	0.828	-161	4.74	57	0.027	-22	0.638	-144
0.550	0.832	-162	4.47	55	0.026	-22	0.648	-145
0.575	0.835	-163	4.23	53	0.027	-24	0.658	-146
0.600	0.838	-164	4.01	51	0.025	-26	0.669	-147
0.625	0.842	-165	3.81	50	0.025	-26	0.678	-148
0.650	0.844	-166	3.61	48	0.024	-25	0.687	-150
0.675	0.848	-167	3.43	46	0.023	-28	0.697	-150
0.700	0.851	-168	3.27	44	0.023	-30	0.706	-151
0.725	0.855	-168	3.12	43	0.022	-30	0.714	-152
0.750	0.858	-169	2.97	41	0.021	-31	0.723	-153
0.775	0.861	-170	2.84	39	0.021	-31	0.731	-154
0.800	0.863	-170	2.72	38	0.020	-32	0.738	-155
0.825	0.866	-171	2.60	36	0.019	-33	0.746	-156
0.850	0.870	-172	2.49	35	0.018	-34	0.754	-157
0.875	0.871	-173	2.38	33	0.018	-34	0.763	-158
0.900	0.875	-173	2.29	32	0.017	-35	0.768	-159
0.925	0.877	-174	2.20	30	0.016	-36	0.776	-160
0.950	0.879	-175	2.11	29	0.016	-36	0.782	-161
0.975	0.883	-175	2.03	28	0.016	-34	0.787	-161
1.000	0.885	-176	1.95	27	0.015	-34	0.793	-162

Table 5. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 500$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.832	-162	5.08	60	0.025	-17	0.612	-145
0.525	0.834	-162	4.80	58	0.025	-20	0.624	-146
0.550	0.838	-164	4.53	56	0.024	-21	0.635	-147
0.575	0.840	-164	4.29	54	0.024	-21	0.644	-148
0.600	0.844	-165	4.07	52	0.023	-23	0.655	-149
0.625	0.847	-166	3.86	50	0.023	-24	0.664	-150
0.650	0.849	-167	3.66	48	0.022	-25	0.673	-151
0.675	0.852	-168	3.48	46	0.021	-27	0.682	-152
0.700	0.856	-169	3.32	45	0.021	-28	0.690	-153
0.725	0.858	-170	3.17	43	0.020	-28	0.701	-154
0.750	0.861	-170	3.02	41	0.019	-30	0.709	-154
0.775	0.864	-171	2.89	40	0.019	-29	0.716	-155
0.800	0.866	-172	2.76	38	0.018	-29	0.723	-156
0.825	0.869	-172	2.65	37	0.017	-29	0.733	-157
0.850	0.872	-173	2.53	35	0.017	-31	0.742	-158
0.875	0.874	-174	2.43	34	0.016	-31	0.751	-159
0.900	0.878	-175	2.33	32	0.015	-31	0.757	-160
0.925	0.879	-175	2.24	31	0.015	-32	0.763	-161
0.950	0.881	-176	2.15	29	0.014	-31	0.770	-161
0.975	0.884	-176	2.07	28	0.014	-31	0.775	-162
1.000	0.886	-177	2.00	27	0.013	-30	0.781	-163

PACKAGE DIMENSIONS



- NOTES:
1. CONTROLLING DIMENSIONS: INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSION H (PACKAGE COPLANARITY): THE BOTTOM OF LEADS AND REFERENCE PLANE T MUST BE COPLANAR WITHIN DIMENSION H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.180	0.190	4.572	4.830
B	0.140	0.150	3.556	3.810
C	0.082	0.116	2.083	2.946
D	0.047	0.053	1.194	1.346
E	0.004	0.010	0.102	0.254
F	0.004	0.006	0.102	0.152
H	0.000	0.004	0.000	0.102
K	0.050	0.090	1.270	2.286
M	0.197	0.203	5.004	5.156
N	0.177	0.183	4.496	4.648
R	0.147	0.153	3.734	3.886
S	0.157	0.163	3.988	4.140
Y	0.020	0.040	0.508	1.016
Z	---	R.020	---	R.508
bbb	.010 REF		0.254 REF	
ccc	.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

**CASE 458C-03
ISSUE D
NI-200Z**

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MRF6522-10/D